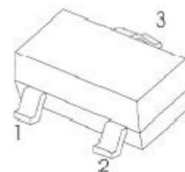
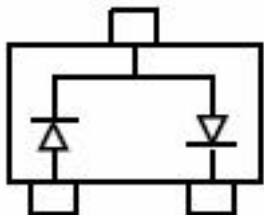


SCHOTTKY BARRIER DIODE

FEATURES

Extremely Fast Switching Speed
Low forward voltage

MARKING:KL8



SOT323

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}	30	V
Working Peak Reverse Voltage	V _{RWM}		
	V _R		
Forward Continuous Current	I _{FM}	200	mA
Power Dissipation	P _D	200	mW
Storage temperature	T _{STG}	-55-150	°C

Electrical Characteristics @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}	30			V	I _R =100μA
Forward voltage	V _{F1}			0.24	V	I _F =0.1mA
	V _{F2}			0.32	V	I _F =1mA
	V _{F3}			0.40	V	I _F =10mA
	V _{F4}			0.50	V	I _F =30mA
	V _{F5}			1	V	I _F =100mA
Reverse current	I _R			2	μA	V _R =25V
Diode Capacitance	C _D			10	pF	V _R =1V, f=1MHz
Reverse Recovery Time	t _{rr}			5	nS	I _F =I _R =10mA I _{rr} =0.1X I _R , R _L =100Ω

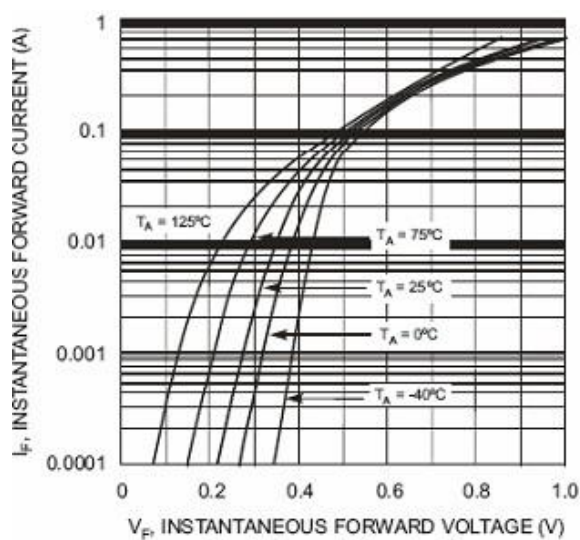


Fig. 1 Forward Characteristics

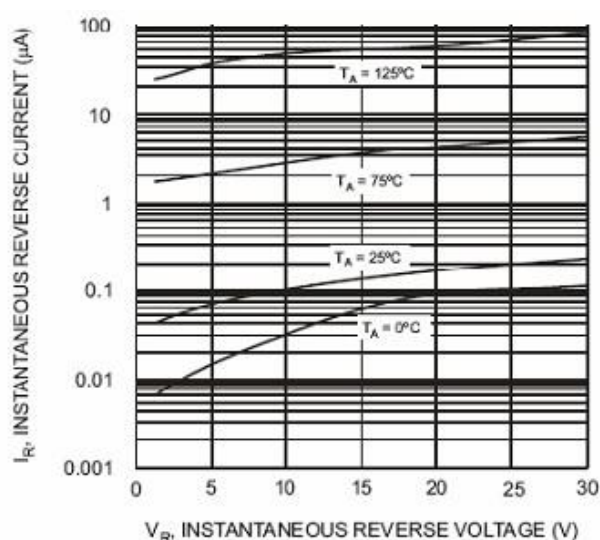


Fig. 2 Typical Reverse Characteristics

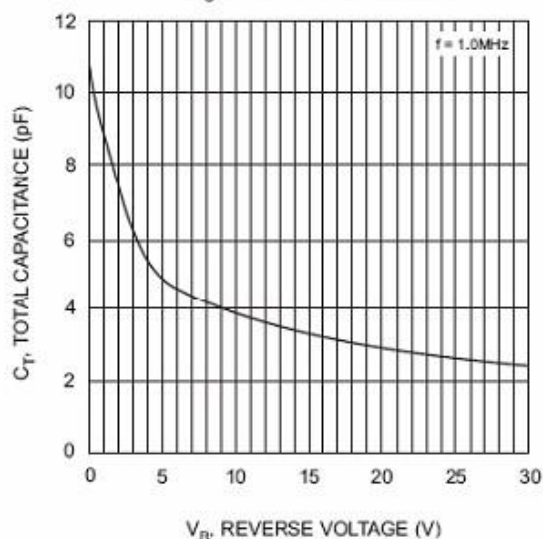


Fig. 3 Typical Capacitance vs. Reverse Voltage

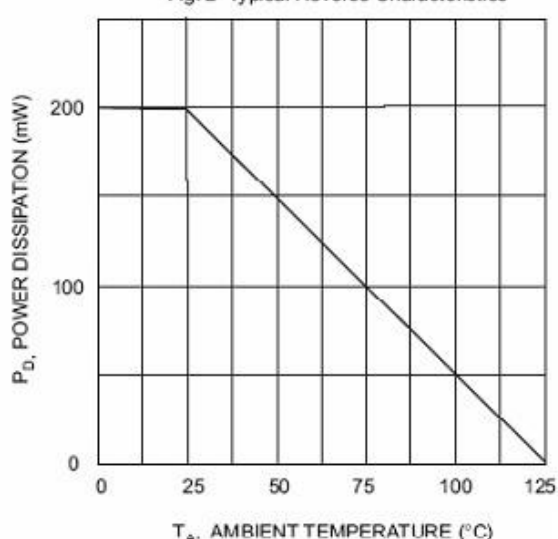
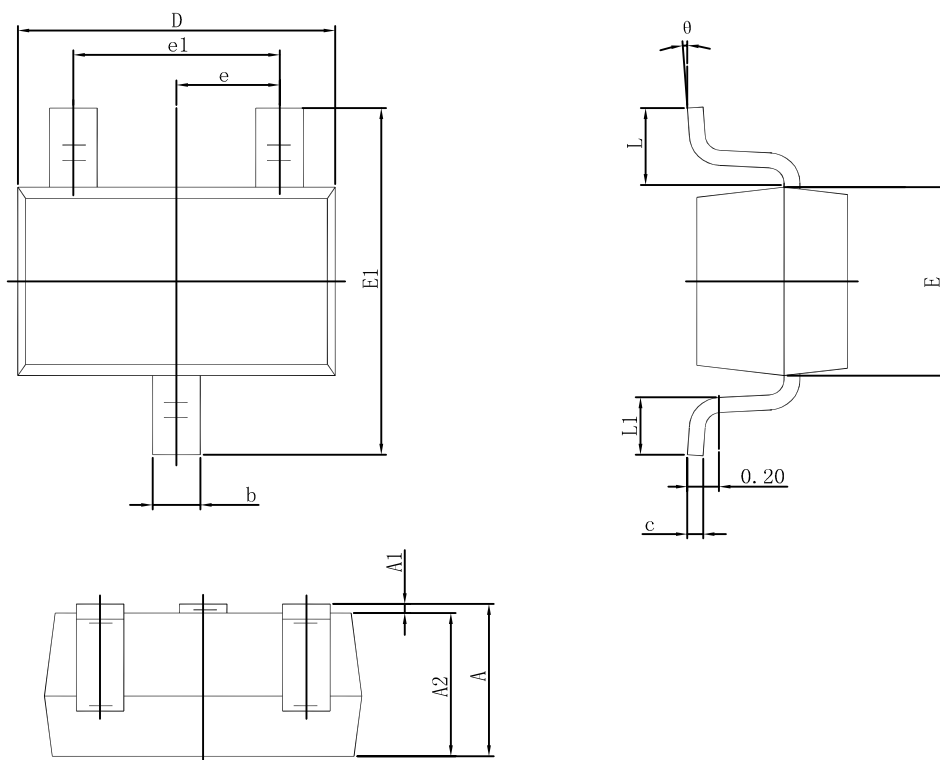


Fig. 4 Power Derating Curve

SOT323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°